

isc N-Channel MOSFET Transistor

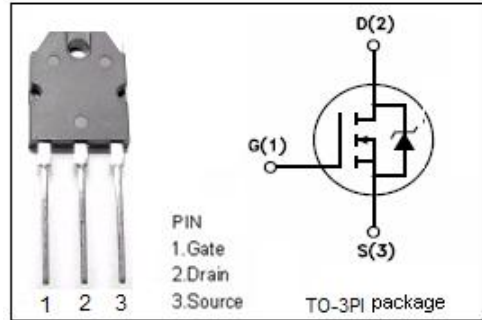
2SK1358

DESCRIPTION

- Drain Current $-I_D = 9A @ T_C = 25^\circ C$
- Drain Source Voltage-
: $V_{DSS} = 900V(\text{Min})$
- Fast Switching Speed

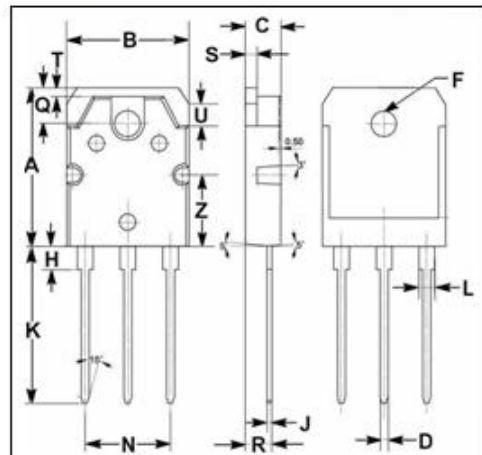
APPLICATIONS

- Designed for high voltage, high speed power switching



ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS} = 0$)	900	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-continuous @ $T_C = 25^\circ C$	9	A
P_{tot}	Total Dissipation @ $T_C = 25^\circ C$	150	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.50	15.70
C	4.40	4.60
D	0.90	1.10
F	3.20	3.40
H	2.90	3.10
J	0.50	0.70
K	19.90	20.10
L	1.90	2.10
N	10.80	11.00
Q	4.40	4.60
R	3.30	3.35
S	1.40	1.60
T	1.00	1.20
U	2.10	2.30
Z	8.90	9.10

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	0.833	$^\circ C/W$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	50	$^\circ C/W$

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• ELECTRICAL CHARACTERISTICS (T_C=25°C)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0; I _D = 10mA	900			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =10 V _{GS} ; I _D =1mA	1.5		3.5	V
R _{DS(on)}	Drain-Source On-stage Resistance	V _{GS} =10V; I _D =4A		1.1	1.4	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±25V; V _{DS} = 0			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =720V; V _{GS} = 0			300	uA
V _{SD}	Diode Forward Voltage	I _F =9A; V _{GS} =0			2.0	V
t _r	Rise time	V _{GS} =10V; I _D =4A; R _L =100 Ω		25	50	ns
t _{on}	Turn-on time			40	80	ns
t _f	Fall time			20	40	ns
t _{off}	Turn-off time			100	200	ns